

# **Device Modeling Report**

**COMPONENTS:**

DIODE/ GENERAL PURPOSE RECTIFIER / STANDARD

PART NUMBER: RHP30120

MANUFACTURER: INTERSIL

REMARK: TC=110C

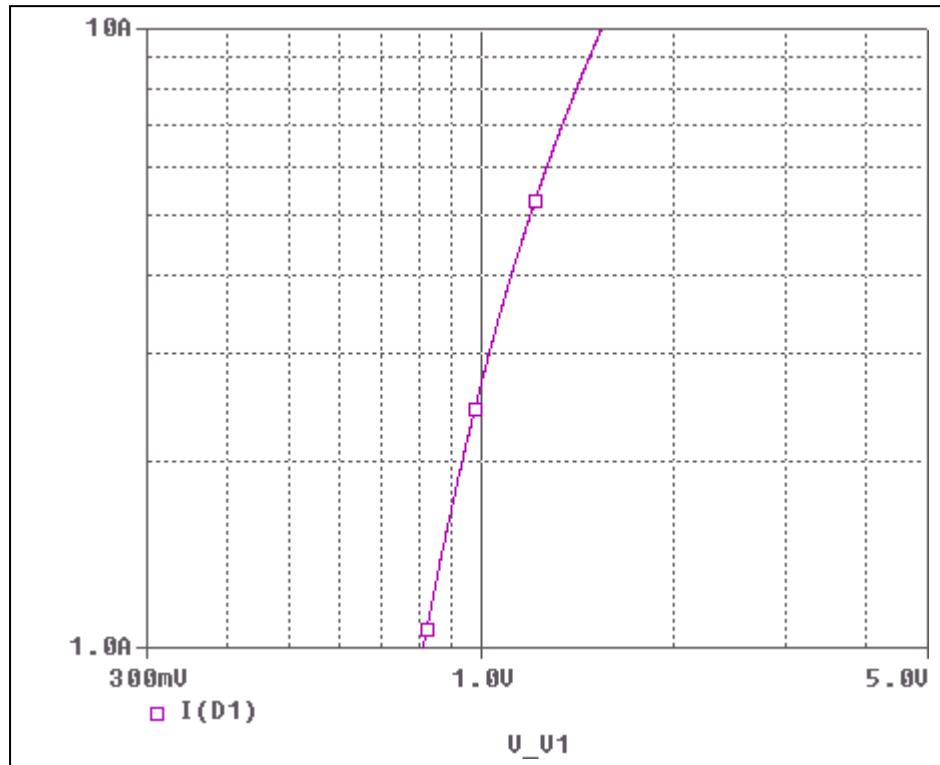


**Bee Technologies Inc.**

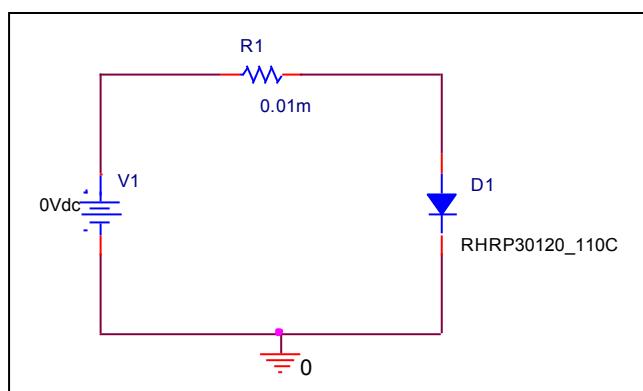
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

## Forward Current Characteristic

### Circuit Simulation Result

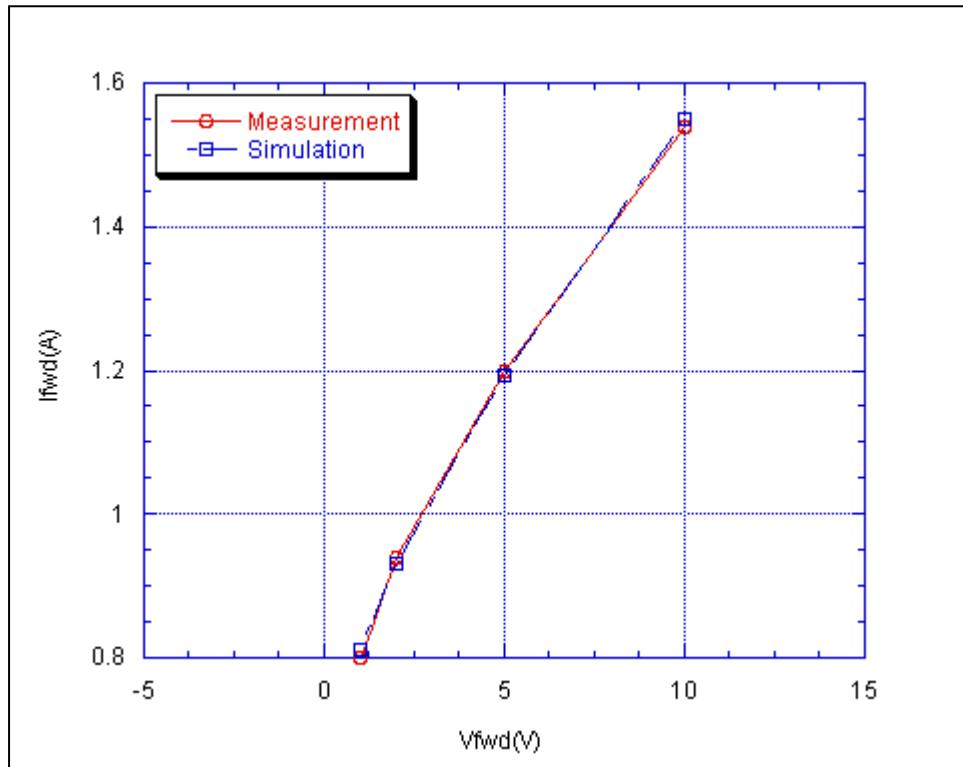


### Evaluation Circuit



## Comparison Graph

Circuit Simulation Result

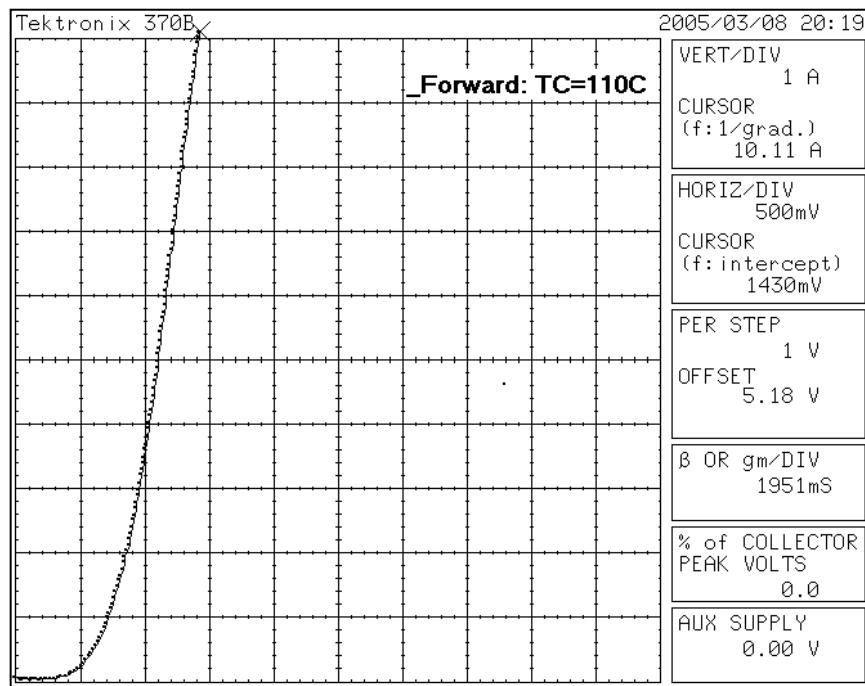


Simulation Result

$I_{fwd}$ (A)	$V_{fwd}$ (V) Measurement	$V_{fwd}$ (V) Simulation	%Error
1	0.800	0.811	-1.38
2	0.940	0.933	0.80
5	1.200	1.193	0.63
10	1.540	1.550	-0.64

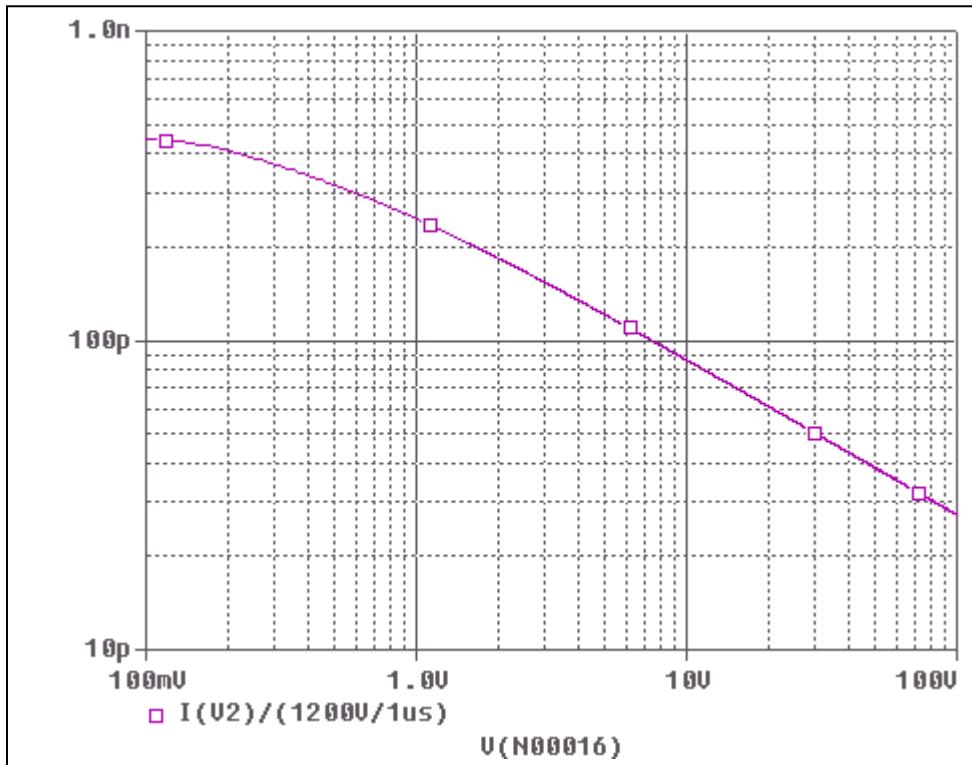
## Forward Current Characteristic

## Reference

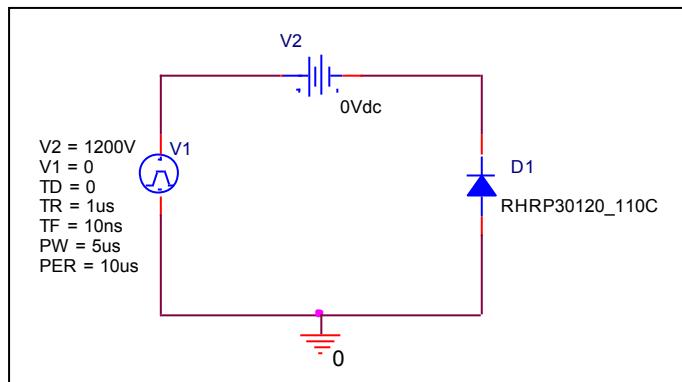


## Capacitance Characteristic

### Circuit Simulation Result

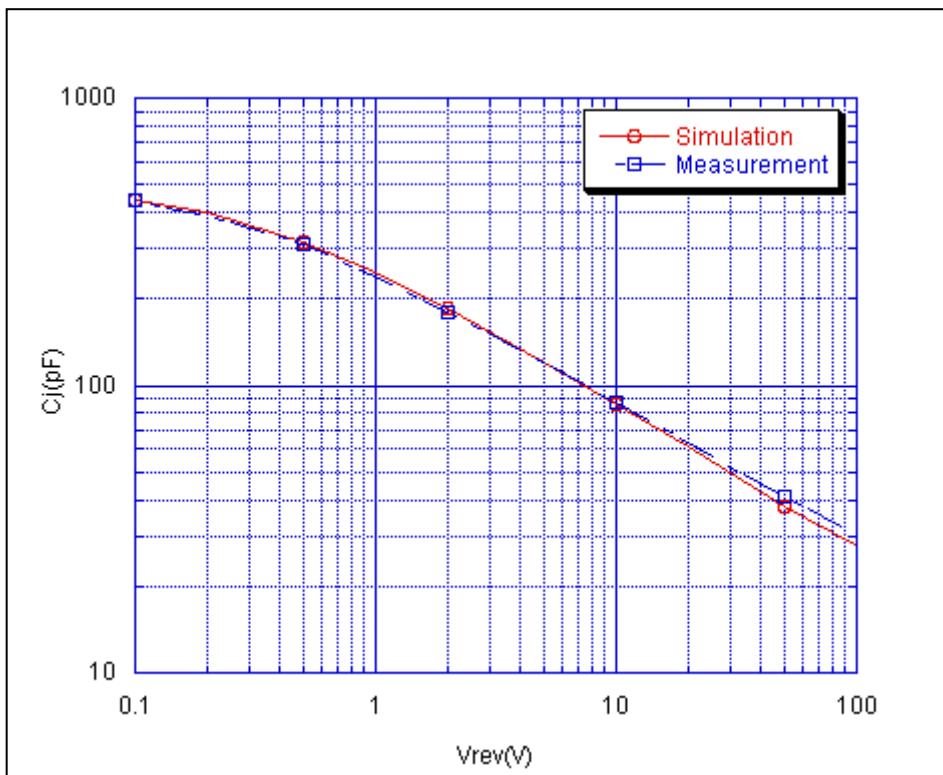


### Evaluation Circuit



## Comparison Graph

### Circuit Simulation Result

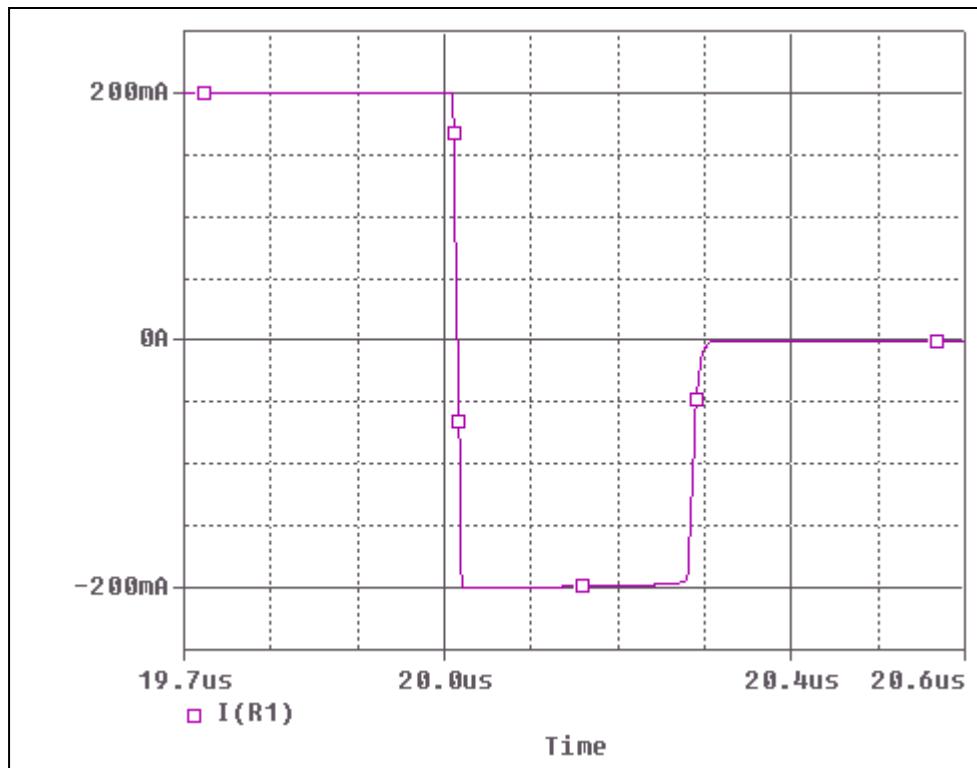


### Simulation Result

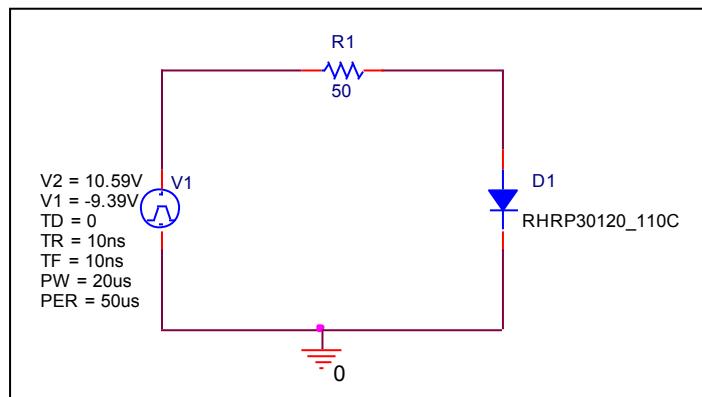
$V_{\text{rev}}(\text{V})$	$C_j(\text{pF})$ Measurement	$C_j(\text{pF})$ Simulation	%Error
0	486.000	486.000	0.00
0.1	440.000	442.203	-0.50
0.2	390.000	401.496	-2.95
0.5	308.000	315.614	-2.47
1	240.000	246.984	-2.91
2	180.000	184.319	-2.40
5	120.000	120.395	-0.33
10	88.000	86.394	1.82
20	63.000	61.207	2.85

## Reverse Recovery Characteristic

### Circuit Simulation Result



### Evaluation Circuit

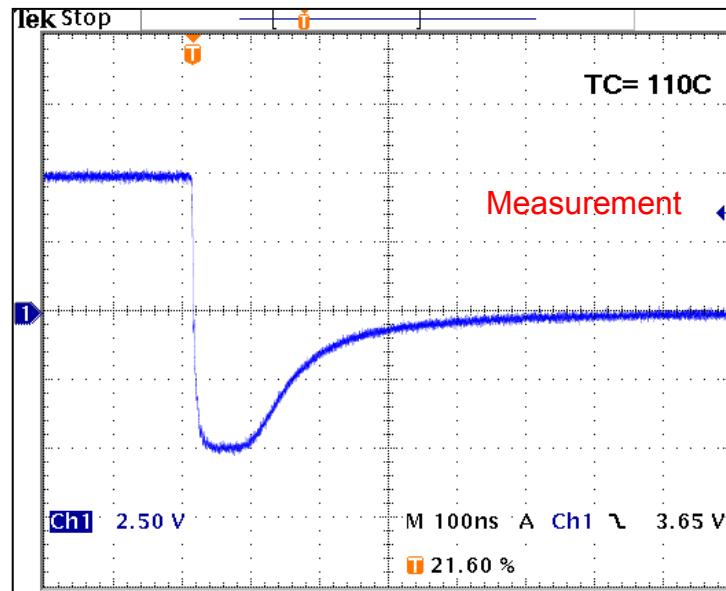


### Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trr	280	ns	279.65	ns	0.125

## Reverse Recovery Characteristic

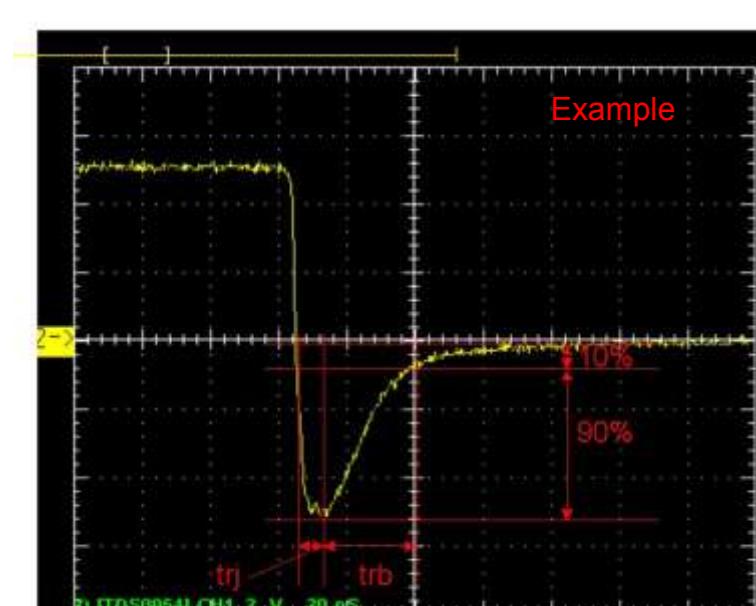
Reference



Trj =70 (ns)

Trb=210 (ns)

Conditions: Ifwd=Irev=0.2(A), RI=50



Relation between trj and trb